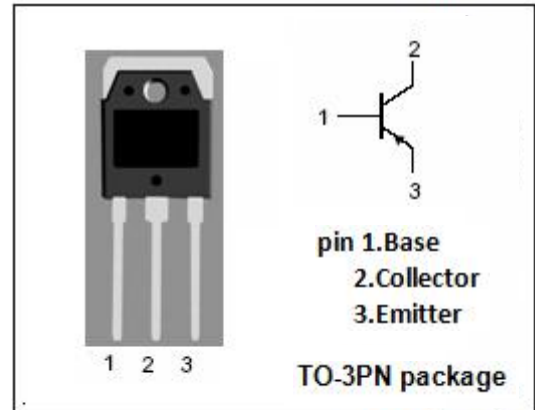


Silicon PNP Power Transistor
MJ21195
DESCRIPTION

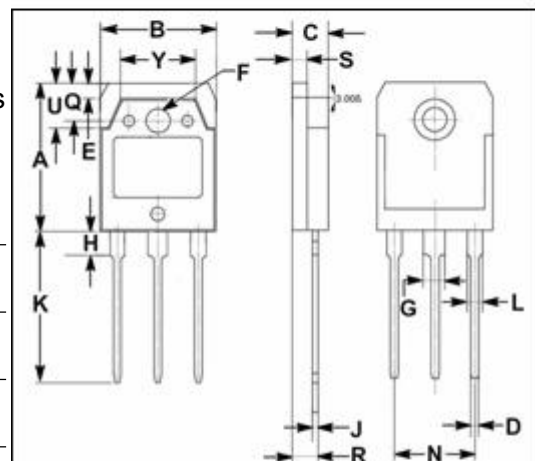
- Excellent Safe Operating Area
- DC Current Gain-
: $h_{FE} = 25-75 @ I_C = -8A, V_{CE} = -5V$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.4 V(\text{Max}) @ I_C = -8A$
- Complement to the PNP MJ21196
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- Designed for high power audio output, disk head positioners and other linear applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | -400 | V |
| V_{CEO} | Collector-Emitter Voltage | -250 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current-Continuous | -16 | A |
| I_B | Base Current | -5 | A |
| P_D | Total Power Dissipation@ $T_C=25^\circ\text{C}$ | 200 | W |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -65~150 | $^\circ\text{C}$ |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 19.60 | 20.30 |
| B | 15.50 | 15.70 |
| C | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| H | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 19.80 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.20 |
| Y | 9.90 | 10.10 |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------|--------------------------------------|-----|---------------------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 0.7 | $^\circ\text{C}/\text{W}$ |

Silicon PNP Power Transistor

MJ21195

ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|------------------------|--------------------------------------|---|------|------|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = -50mA ; I _B = 0 | -250 | | V |
| V _{CE(sat)-1} | Collector-Emitter Saturation Voltage | I _C = -8A; I _B = -0.8A | | -1.4 | V |
| V _{CE(sat)-2} | Collector-Emitter Saturation Voltage | I _C = -16A; I _B = -3.2A | | -4.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -8A ; V _{CE} = -5V | | -2.2 | V |
| I _{CEO} | Collector Cutoff Current | V _{CE} = -200V; V _{BE(off)} = 0 | | -0.1 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | -0.1 | mA |
| h _{FE-1} | DC Current Gain | I _C = -8A ; V _{CE} = -5V | 25 | 75 | |
| h _{FE-2} | DC Current Gain | I _C = -16A ; V _{CE} = -5V | 8 | | |

NOTICE:

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